

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage (Note 5)			V _{GSS}	±12	V
Continuous Drain Current (Note 7) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	6.8 5.8	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	8.8 7.0	A
Maximum Body Diode Forward Current (Note 7)			I _S	2	A
Pulsed Drain Current (10μs pulse, Duty cycle = 1%)			I _{DM}	40	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 6)			P _D	1.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state		R _{θJA}	118	°C/W
	t < 10s			72	
Total Power Dissipation (Note 7)			P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady state		R _{θJA}	82	°C/W
	t < 10s			50	
Thermal Resistance, Junction to Case (Note 7)			R _{θJC}	14	
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±10V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	0.5	—	1	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	16	20	mΩ	V _{GS} = 10V, I _D = 4A
			17	22		V _{GS} = 4.5V, I _D = 4A
			19	26		V _{GS} = 2.5V, I _D = 4A
			24	36		V _{GS} = 1.8V, I _D = 4A
Forward Transfer Admittance	Y _{fs}	—	8	—	S	V _{DS} = 5V, I _D = 12A
Diode Forward Voltage	V _{SD}	—	0.7	1.0	V	V _{GS} = 0V, I _S = 5A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	151	—	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	91	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	32	—	pF	
Gate Resistance	R _g	—	200	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	8.5	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 6.5A
Gate-Source Charge	Q _{gs}	—	1.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	2.8	—	nC	
Turn-On Delay Time	t _{D(on)}	—	53	—	ns	V _{GS} = 10V, V _{DS} = 4.5V, R _G = 6Ω, R _L = 1.0Ω, I _D = 1A
Turn-On Rise Time	t _r	—	77	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	561	—	ns	
Turn-Off Fall Time	t _f	—	234	—	ns	

- Notes:
- AEC-Q101 V_{GS} maximum is ±9.6V.
 - Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

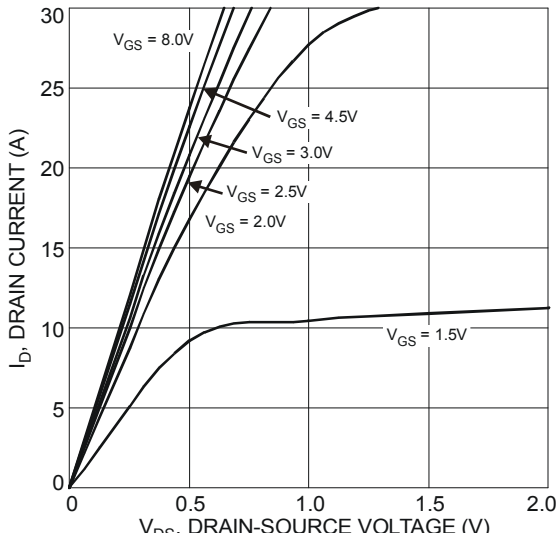


Figure 1 Typical Output Characteristic

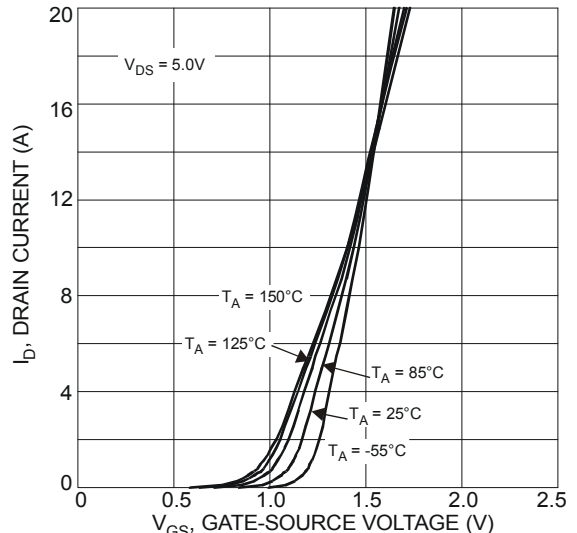


Figure 2 Typical Transfer Characteristics

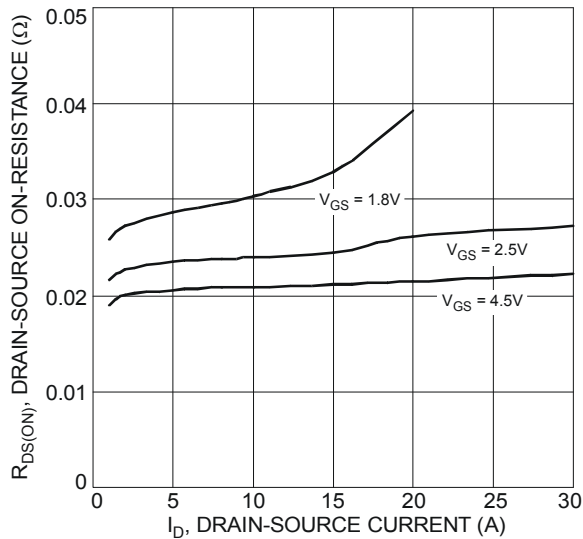


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

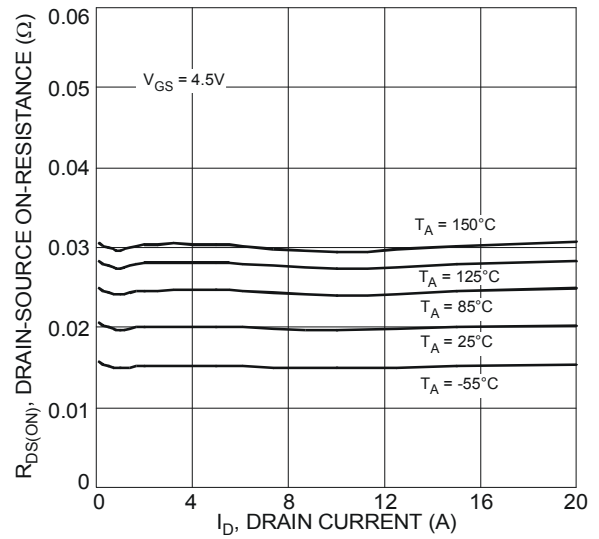


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

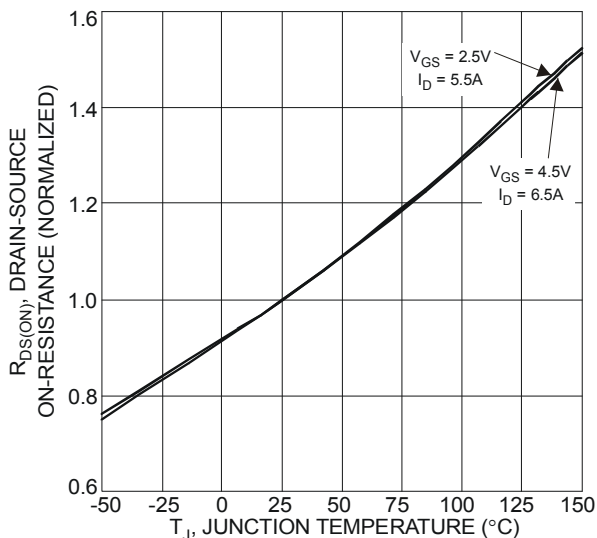


Figure 5 On-Resistance Variation with Temperature

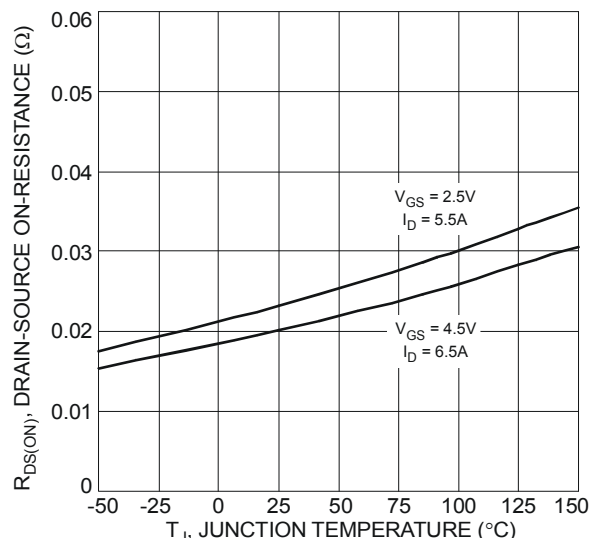


Figure 6 On-Resistance Variation with Temperature

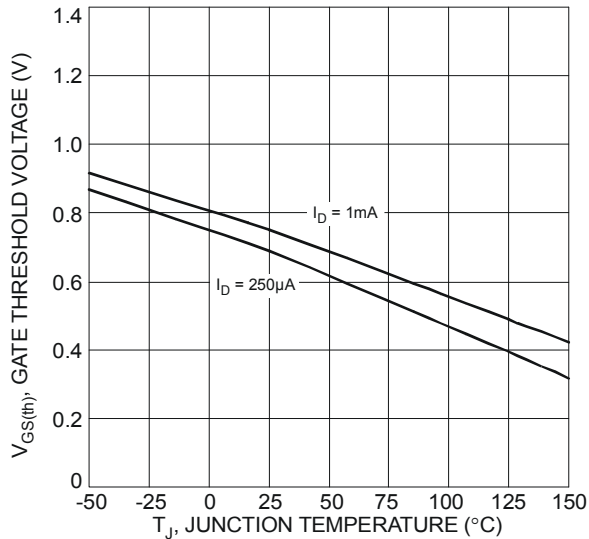


Figure 7 Gate Threshold Variation vs. Ambient Temperature

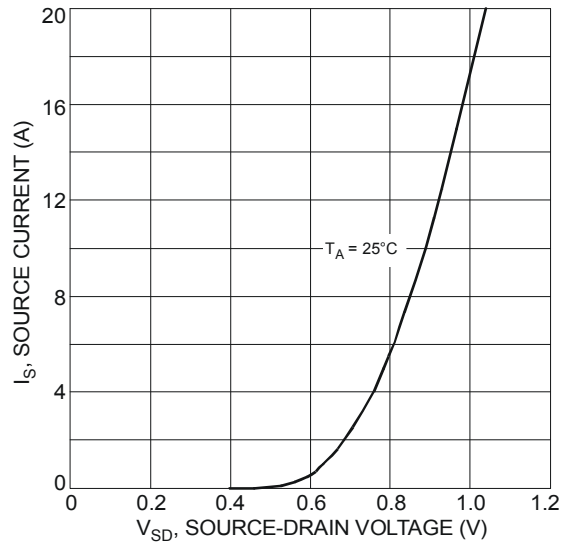


Figure 8 Diode Forward Voltage vs. Current

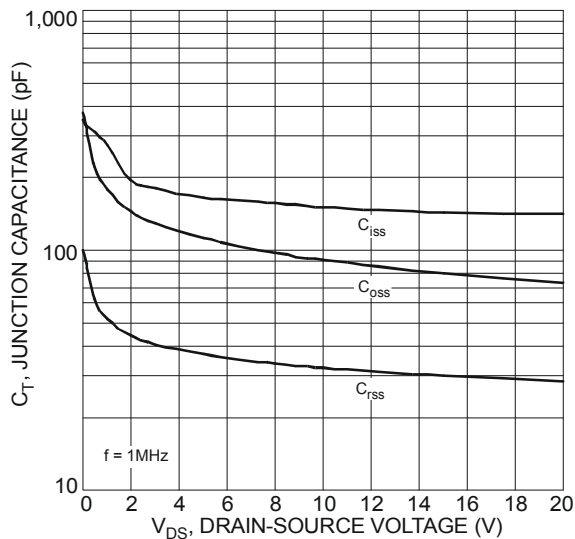


Figure 9 Typical Junction Capacitance

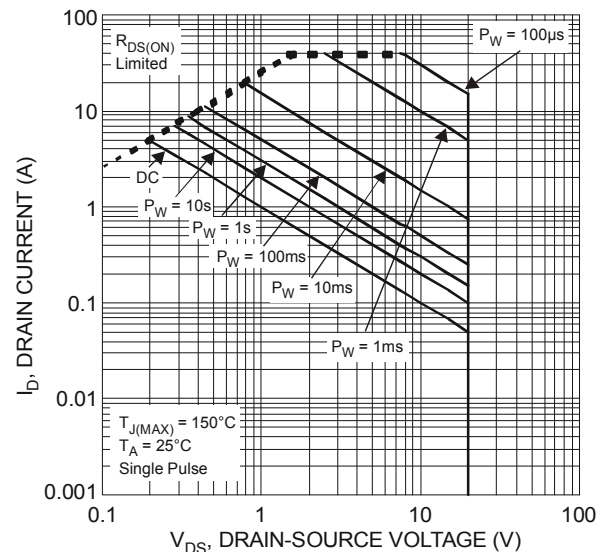


Figure 10 SOA, Safe Operation Area

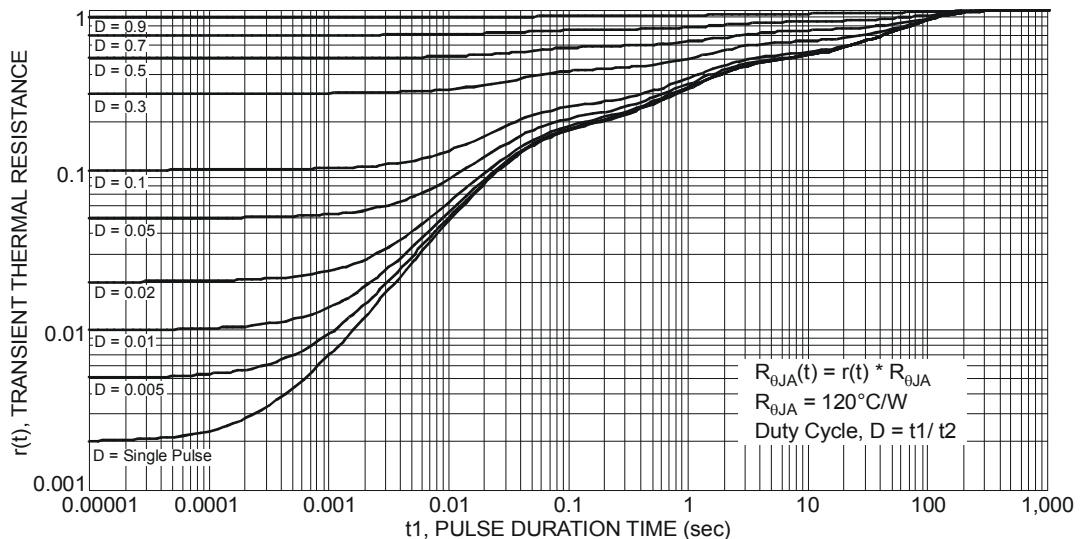
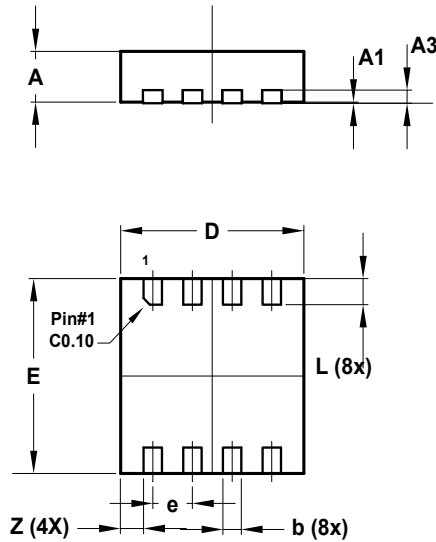


Figure 11 Transient Thermal Resistance

Package Outline Dimensions

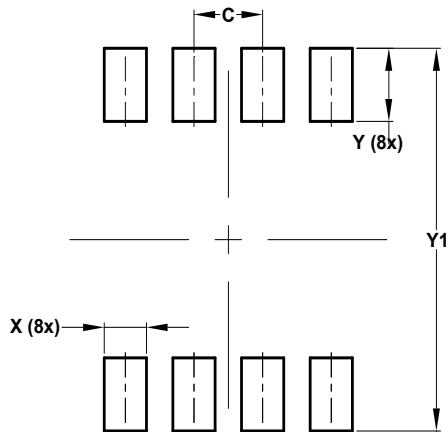
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



POWERDI3030-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0	0.05	0.02
A3	-	-	0.203
b	0.25	0.35	0.30
D	2.95	3.05	3.00
E	2.95	3.05	3.00
e	-	-	0.65
L	0.55	0.65	0.60
Z	-	-	0.375
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
X	0.400
Y	0.850
Y1	3.400

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